



FORM PTO-1449 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE INFORMATION DISCLOSURE STATEMENT BY APPLICANT (USE SEVERAL SHEETS IF NECESSARY)	ATTY. DOCKET NO. ASMJP.065AUS	APPLICATION NO. 09/779,397
	APPLICANT Michael A. Todd	
	FILING DATE February 7, 2001	

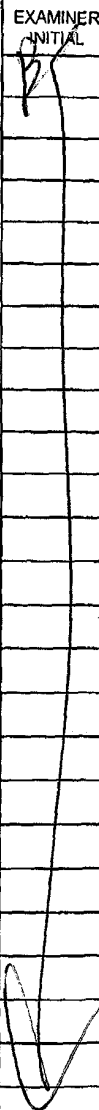
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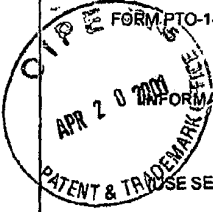
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U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
	1.	4,781,942	11/01/88	Leyden et al.			
	2.	4,863,755	09/05/89	Hess et al.			
	3.	4,894,352	01/16/90	Lane et al.			
	4.	4,992,306	02/12/91	Hochberg et al.			
	5.	5,011,706	04/30/91	Tarhay et al.			
	6.	5,028,566	07/02/91	Legendijk			
	7.	5,231,058	07/27/93	Maeda et al.			
	8.	5,240,813	08/31/93	Watanabe et al.			
	9.	5,314,724	05/24/94	Tsukune et al.			
	10.	5,324,539	06/28/94	Maeda et al.			
	11.	5,380,555	01/10/95	Mine et al.			
	12.	5,433,786	07/18/95	Hu et al.			
	13.	5,494,712	02/27/96	Hu et al.			
	14.	5,554,570	09/10/96	Maeda et al.			
	15.	5,563,105	10/08/96	Dobuzinsky et al.			
	16.	5,703,404	12/30/97	Matsuura			
	17.	5,840,821	11/24/98	Nakano et al.			
	18.	5,876,798	03/02/99	Vassiliev			
	19.	5,989,998	11/23/99	Sugahara et al.			
	20.	5,998,522	12/07/99	Nakano et al.			
	21.	6,045,877	04/04/00	Gleason et al.			
	22.	6,051,321	04/18/00	Lee et al.			
	23.	6,051,508	04/18/00	Takase et al.			
	24.	6,054,379	04/25/00	Yau et al.			
	25.	6,068,884	05/30/00	Rose et al.			

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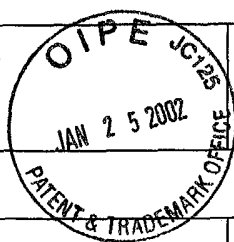
FOREIGN PATENT DOCUMENTS								
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
	26.	WO 97/40207	10/30/97	PCT			X	
	27.	WO 99/55526	11/04/99	PCT			X	
	28.	EPO 367 004 B1	12/15/93	EPO			X	
	29.	EP 0 436 185 B1	03/20/96	EPO			X	
	30.	EP 0 723 600 B1	07/07/99	EPO			X	
	31.	EP 0 771 886 A1	05/07/97	EPO			X	
	32.	EP 0 935 283 A2	08/11/99	EPO			X	
	33.	EP 0 960 958 A2	12/01/99	EPO			X	

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)	
	34.	Bayer et al., Overall kinetics of SiO <sub>x</sub> remote-PECVD using different organosilicon monomers, Surface and Coatings Technology, 116-119 (1996) 874-878
	35.	Benjoan et al., XPS and XPS valence band characterizations of amorphous or polymeric silicon based thin films prepared by PACVD from organosilicon monomers, J. Phys. IV France 9 (1999) pp. 1059-1068.
	36.	Constant et al., Some Properties of amorphous Si <sub>3</sub> C <sub>1-x</sub> (H) alloys prepared by CVD from various organosilicon compounds, Solid State Chemistry, 1982, pp. 267-270
	37.	Deville et al., An AES study of the influence of carbon on the chemical structure of some oxide films deposited by PECVD of organosilicon precursors, Applied Surface Science 137 (1999) 136-141
	38.	Fonseca et al., Plasma Polymerization of Tetramethylsilane, Am. Chemical Society, 1993, 5, 1676-1682
	39.	Inoue et al., Mass spectroscopy in plasma-enhanced chemical vapor deposition of silicon-oxide films using tetramethoxysilane, Thin Solid Films 316 (1998) 79-84
	40.	Inoue et al., Spectroscopic studies on preparation of silicon oxide films by PECVD using organosilicon compounds, Plasma Sources Sci. Technol. 5 (1998) 339-343
	41.	Loboda, M.J., New solutions for intermetal dielectrics using trimethylsilane-based PECVD processes, Microelectronic Engineering 50 (2000) 15-23
	42.	Nguyen et al., Plasma organosilicon polymers, J. Electrochem. Soc., August 1985, pp. 1925-1932
	43.	Shirafuji et al., PE-CVD of Fluorocarbon/SiO composite thin films using C <sub>4</sub> F <sub>8</sub> and HMDSO <sub>1</sub> , Plasmas and Polymers, Vo. 4, No. 1, 1999, pp. 57-75
	44.	Shirafuji et al., PE-CVD of fluorocarbon/silicon oxide composite thin films from TFE and HMDSO, Mat. Res. Soc. Symp. Proc. Vol. 544, pp. 173-178 (1999)
	45.	Shirafuji et al., Plasma copolymerization of tetrafluoroethylene/hexamethyldisiloxane and In Situ Fourier Transform infrared spectroscopy of its gas phase, Jpn. J. Appl. Phys. Vol. 38 (1999) pp. 4520-4528
	46.	Sugahara et al., Low Dielectric constant carbon containing SiO <sub>2</sub> films deposited by PECVD technique using a novel CVD precursor, DUMIC Conference, Feb. 10-11, 1997, pp. 19-25
	47.	Thomas et al., Plasma etching and surface analysis of a SiC:H films deposited by low temperature plasma enhanced chemical vapor deposition, Mat. Res. Soc. Symp. Proc. Vol. 334, 1994, pp. 445-450
	48.	Matsuki, N., U.S. Patent Application No. 09/249,456-Silicone-Polymer-insulation-film-on-semiconductor-substrate-and-method-for-forming-the-film, filed February 2, 1999. NOT A PUBLICATION

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EXAMINER INITIALS	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)	
✓	1.	Indrajit Banerjee, et al., "Characterization of Chemical Vapor Deposited Amorphous Fluorocarbons for Low Dielectric Constant Interlayer Dielectrics." J. Electrochem. Soc., Vol. 146(6), p. 2219 (1999).
	2.	Sang-Soo Han, et al., "Deposition of Fluorinated Amorphous Carbon Thin Films as a Low-Dielectric Constant Material." J. Electrochem. Soc., Vol. 146(9), p.3383 (1999).
	3.	H. Beckers, et al., "Synthesis and Properties of (Trifluoromethyl) trichlorosilane, a Versatile Precursor for CF3SI Compounds," J. Organometal. Chem., Vol. 316, pp. 41-50, (1986).
	4.	C.A. Costello and J.J. McCarthy, "Introduction of Organic Functional Groups onto the Surface of Poly(tetrafluoroethylene)," Proceedings of the ACS Division of Polymeric Materials Science and Engineering, Vol. 55 p. 893 (1986).
	5.	K.G. Sharp and T.D. Coyle, "Synthesis and Some Properties of Trifluoro(trifluoromethyl) silane," J. Fluorine Chem., Vol. Q, pp. 249-251 (1971/72).
	6.	Limb, Scott J., et al., "Growth of fluorocarbon polymer thin films with high CF2 fractions and low dangling bond concentrations by thermal chemical vapor deposition," App. Phys. Lett., Vol. 68(20), p. 2810 (1996).
✓	7.	Washburne, Stephen S., et al. "Chloraminosilanes: I: The Preparation of Chloro(Dimethylamino) Hydrogen Silanes," Inorg. Nucl. Chem. Letters Vol. 5, pp. 17-19, Pergamon Press. 1969
	8.	Savage, Charles R., et al., "Spectroscopic Characterization of Films Obtained in Pulsed Radio-Frequency Plasma Discharges of Fluorocarbon Monomers," Structure-Property Relations in Polymers, pp. 745-768, American Chemical Society, (1993).
	9.	Sharp, K.G., et al., "Perfluoro(alkylsilanes). II: Trifluoro(trifluoromethyl) silane and Trifluoro(pentafluoroethyl) silane," Inorg. Chem., Vol. 11, No. 6, pp. 1259-1264, (1972). 1972
	10.	Pam Frest Gorder, "Researchers Pioneer Techniques to Lubricate Microdevices," Research News, Ohio State University, <a href="http://www.acs.ohio-state.edu/units/research/">http://www.acs.ohio-state.edu/units/research/</a> , (3/23/01). Not A Publication

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## FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
	WO 99/60621	11/25/1999	PCT				
	WO 99/41423	08/19/1999	PCT				
	WO 99/21706	05/06/1999	PCT				
	WO 97/41592	11/06/1997	PCT				
	EP 0 706 216 A2	04/10/1996	Europe				

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)	
	A.	PATENT ABSTRACTS OF JAPAN vol. 1998, no. 03, 27 February 1998 (1998-02-27) & JP 09 293716 A (KAWASAKI STEEL CORP), 11 November 1997 (1997-11-11) *abstract*
	B.	PATENT ABSTRACTS OF JAPAN vol. 1999, no.12, 29 October 1999 (1999-10-29) & JP 11 176829 A (INNTECH CORP), 2 July 1999 (1999-07-02) *abstract*
	C.	Chandrasekhar et al., "New Silicon-Carbon Materials Incorporating Si <sub>4</sub> C Building Blocks" Mat. Res. Soc. Symp. Proc. Vol. 441, Materials Research Society (1997)

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